

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

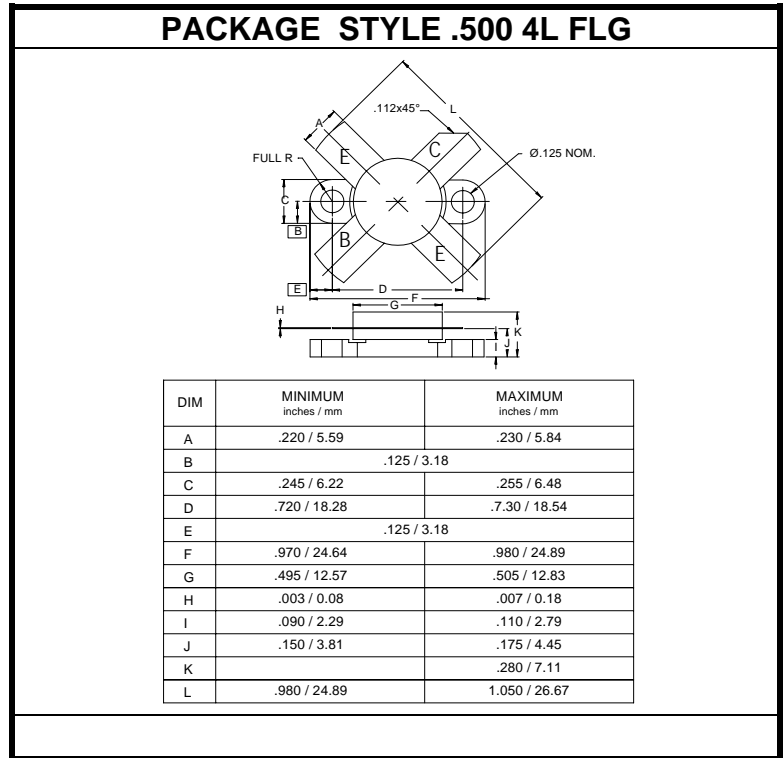
The **ASI MRF429** is Designed for High voltage applications up to 30 MHz

**FEATURES:**

- $P_G = 13$  dB min. at 150 W/30 MHz
- $IMD_3 = -32$  dBc max. at 150 W(PEP)
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	16 A
$V_{CBO}$	100 V
$V_{CEO}$	50 V
$V_{EBO}$	4.0 V
$P_{DISS}$	233 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$\theta_{JC}$	0.75 $^\circ C/W$


**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 100$ mA	100			V
$BV_{CES}$	$I_C = 100$ mA	100			V
$BV_{CEO}$	$I_C = 200$ mA	50			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 5.0$ A	10		80	---
$C_{ob}$	$V_{CB} = 50$ V $f = 1.0$ MHz		220	300	pF
$G_P$		13	15		dB
$IMD$	$V_{CE} = 50$ V $I_{CQ} = 3.3$ A $f = 30$ MHz		-35	-32	dBc
$\eta_C$	$P_{OUT} = 150$ W (PEP)	45			%